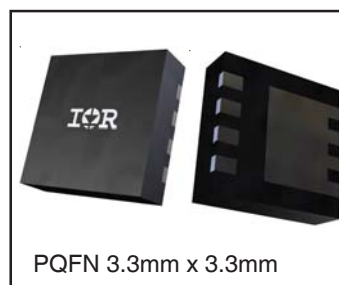
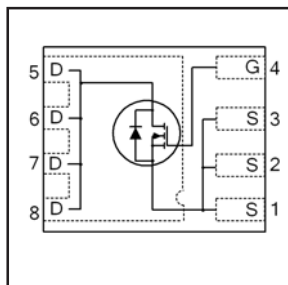


V_{DS}	30	V
R_{DS(on)} max (@ V _{GS} = 10V)	7.8	mΩ
Q_g (typical)	7.3	nC
R_G (typical)	0.5	Ω
I_D (@ T _{C(Bottom)} = 25°C)	40^⑥	A



Applications

- Control MOSFET for Buck Converters

Features and Benefits

Features

Low Charge (typical 7.3nC)
Low Thermal Resistance to PCB (<4.7°C/W)
100% R _g tested
Low Profile (<1.0mm)
Industry-Standard Pinout
Compatible with Existing Surface Mount Techniques
RoHS Compliant Containing no Lead, no Bromide and no Halogen
MSL1, Industrial Qualification

results in
⇒

Benefits

Lower Switching Losses
Enable Better Thermal Dissipation
Increased Reliability
Increased Power Density
Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

Orderable part number	Package Type	Standard Pack		Note
		Form	Quantity	
IRFHM831TRPbF	PQFN 3.3mm x 3.3mm	Tape and Reel	4000	
IRFHM831TR2PbF	PQFN 3.3mm x 3.3mm	Tape and Reel	400	EOL notice # 259

Absolute Maximum Ratings

	Parameter	Max.	Units
V _{DS}	Drain-to-Source Voltage	30	V
V _{GS}	Gate-to-Source Voltage	±20	
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ 10V	14	A
I _D @ T _A = 70°C	Continuous Drain Current, V _{GS} @ 10V	11	
I _D @ T _{C(Bottom)} = 25°C	Continuous Drain Current, V _{GS} @ 10V	40 ^⑥	
I _D @ T _{C(Bottom)} = 100°C	Continuous Drain Current, V _{GS} @ 10V	28	
I _{DM}	Pulsed Drain Current ①	96	W
P _D @ T _A = 25°C	Power Dissipation ⑤	2.5	
P _D @ T _{C(Bottom)} = 25°C	Power Dissipation ⑤	27	
	Linear Derating Factor ⑤	0.02	W/°C
T _J	Operating Junction and	-55 to + 150	°C
T _{STG}	Storage Temperature Range		

Notes ① through ⑥ are on page 9

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

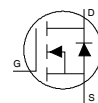
	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.02	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	6.6	7.8	$m\Omega$	$V_{GS} = 10V, I_D = 12A$ ③
		—	10.7	12.6		$V_{GS} = 4.5V, I_D = 12A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.35	1.8	2.35	V	$V_{DS} = V_{GS}, I_D = 25\mu A$
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	—	-6.8	—	mV/ $^\circ\text{C}$	
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 24V, V_{GS} = 0V$
		—	—	150		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
g_{fs}	Forward Transconductance	82	—	—	S	$V_{DS} = 15V, I_D = 12A$
Q_g	Total Gate Charge	—	16	—	nC	$V_{GS} = 10V, V_{DS} = 15V, I_D = 12A$
Q_g	Total Gate Charge	—	7.3	11	nC	$V_{DS} = 15V$ $V_{GS} = 4.5V$ $I_D = 12A$ See Fig.17 & 18
Q_{gs1}	Pre-Vth Gate-to-Source Charge	—	1.7	—		
Q_{gs2}	Post-Vth Gate-to-Source Charge	—	0.9	—		
Q_{gd}	Gate-to-Drain Charge	—	2.5	—		
Q_{godr}	Gate Charge Overdrive	—	2.2	—		
Q_{sw}	Switch Charge ($Q_{gs2} + Q_{gd}$)	—	3.4	—	nC	$V_{DS} = 16V, V_{GS} = 0V$
Q_{oss}	Output Charge	—	5.1	—		
R_G	Gate Resistance	—	0.5	—	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	6.9	—	ns	$V_{DD} = 15V, V_{GS} = 4.5V$ $I_D = 12A$ $R_G = 1.8\Omega$ See Fig.15
t_r	Rise Time	—	12	—		
$t_{d(off)}$	Turn-Off Delay Time	—	6.2	—		
t_f	Fall Time	—	4.7	—		
C_{iss}	Input Capacitance	—	1050	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	190	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	80	—		$f = 1.0MHz$

Avalanche Characteristics

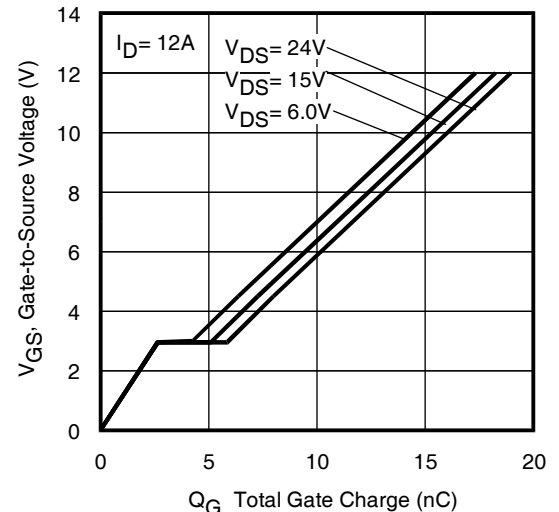
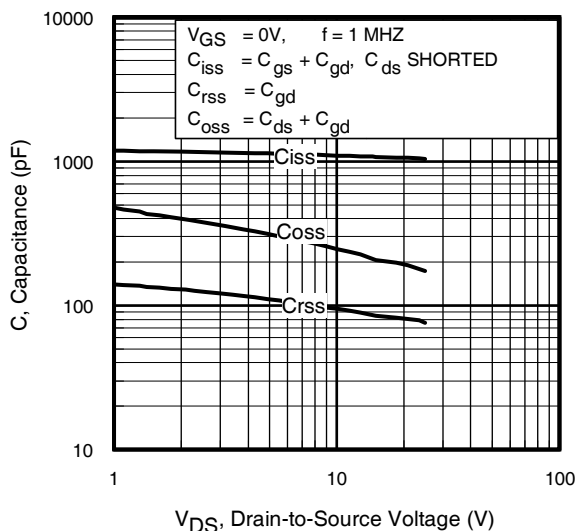
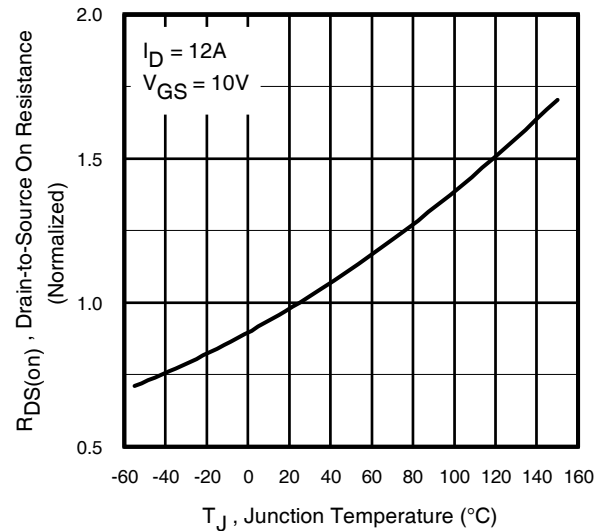
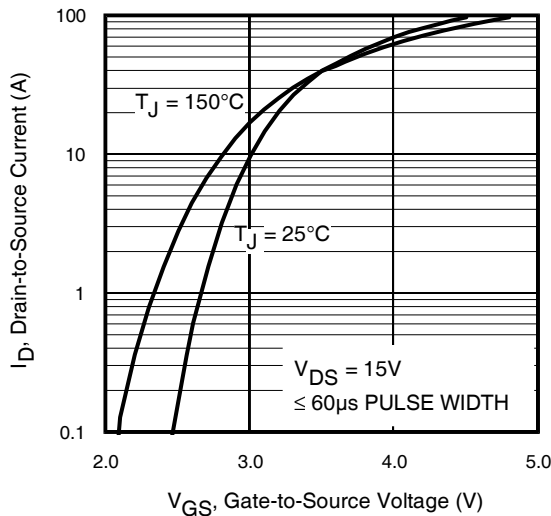
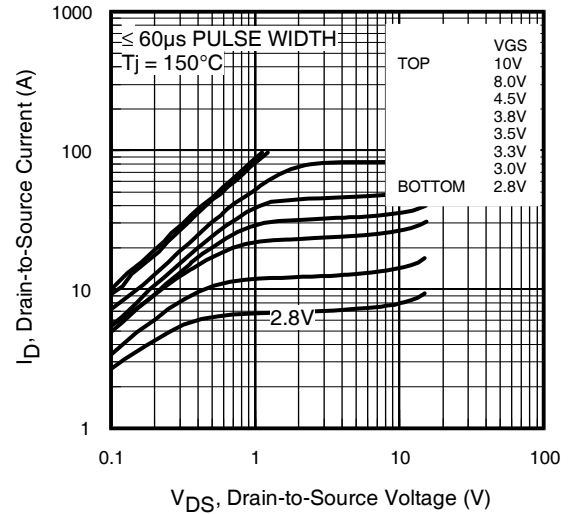
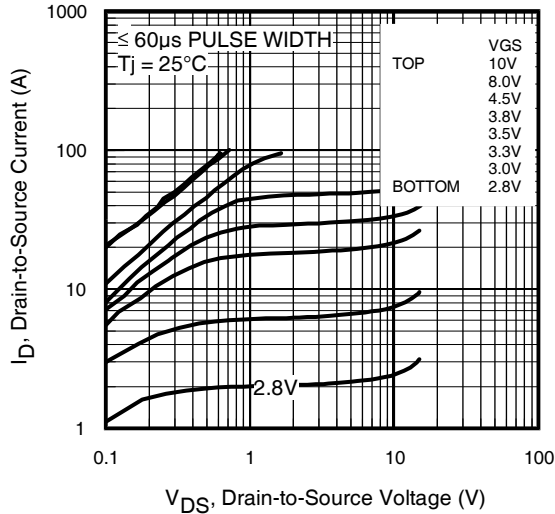
	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	50	mJ
I_{AR}	Avalanche Current ①	—	12	A

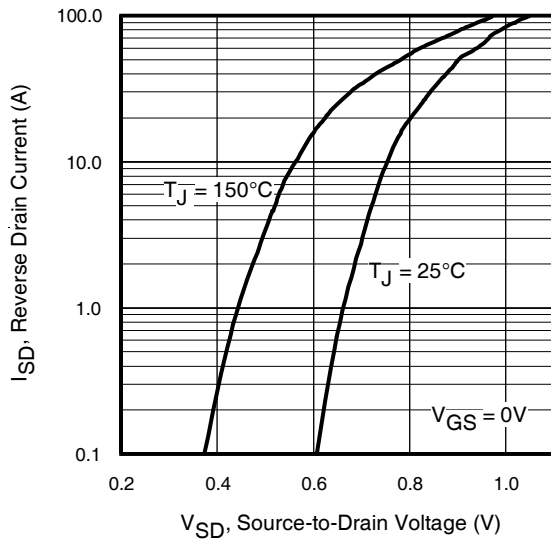
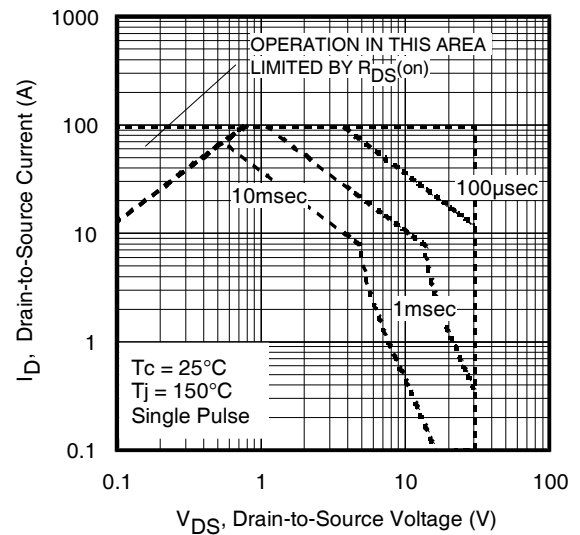
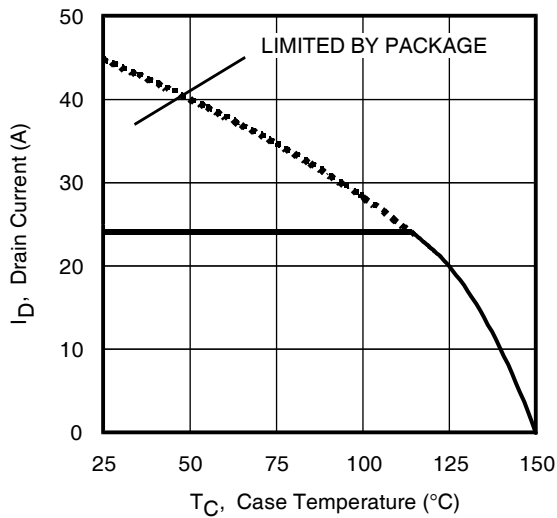
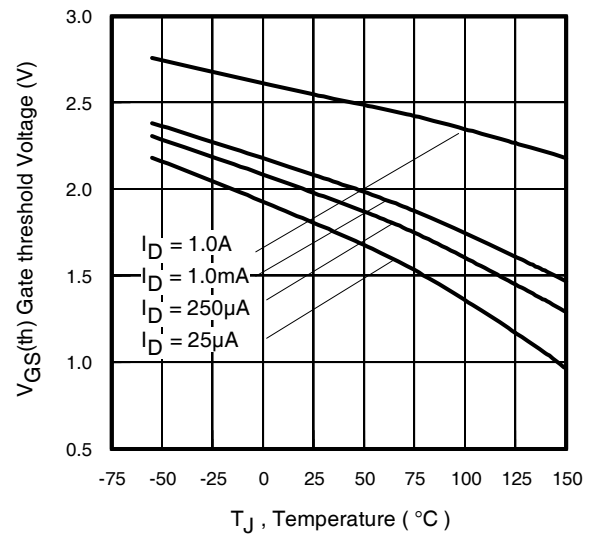
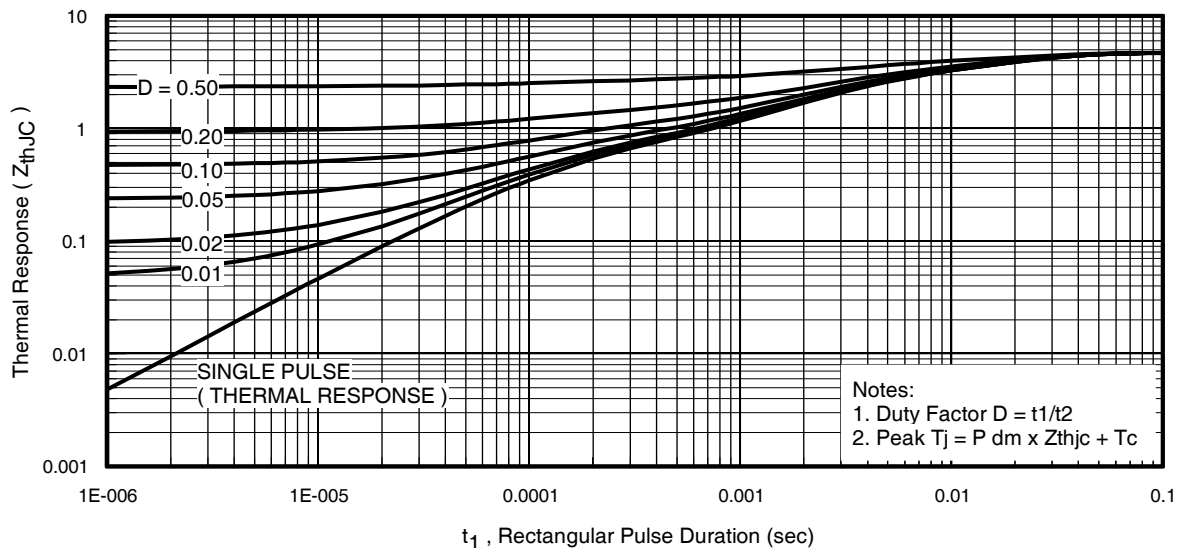
Diode Characteristics

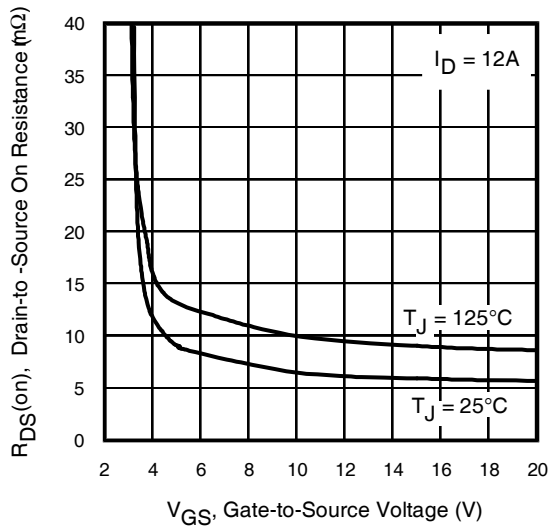
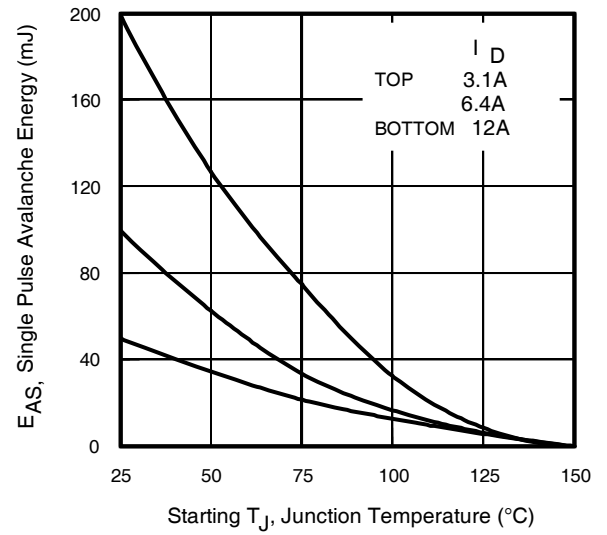
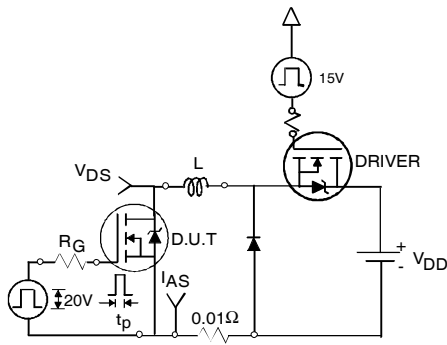
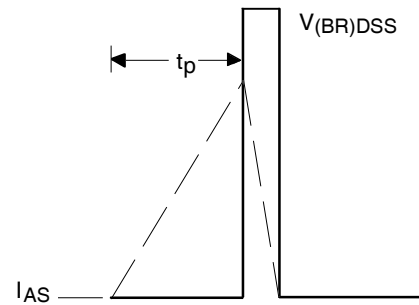
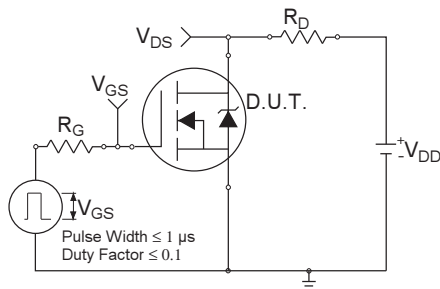
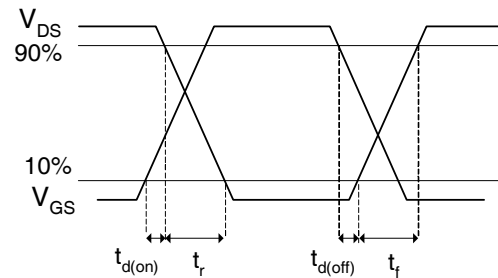
	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	40⑥	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	96		
V _{SD}	Diode Forward Voltage	—	—	1.0	V	T _J = 25°C, I _S = 12A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	—	15	22	ns	T _J = 25°C, I _F = 12A, V _{DD} = 15V di/dt = 300A/μs ③
Q _{rr}	Reverse Recovery Charge	—	16	24	nC	
t _{on}	Forward Turn-On Time	Time is dominated by parasitic Inductance				


Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$ (Bottom)	Junction-to-Case ④	—	4.7	$^\circ\text{C/W}$
$R_{\theta JC}$ (Top)	Junction-to-Case ④	—	44	
$R_{\theta JA}$	Junction-to-Ambient ⑤	—	50	
$R_{\theta JA} (<10s)$	Junction-to-Ambient ⑤	—	32	




Fig 7. Typical Source-Drain Diode Forward Voltage

Fig 8. Maximum Safe Operating Area

Fig 9. Maximum Drain Current Vs. Case (Bottom) Temperature

Fig 10. Threshold Voltage Vs. Temperature

Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case (Bottom)


Fig 12. On-Resistance vs. Gate Voltage

Fig 13. Maximum Avalanche Energy vs. Drain Current

Fig 14a. Unclamped Inductive Test Circuit

Fig 14b. Unclamped Inductive Waveforms

Fig 15a. Switching Time Test Circuit

Fig 15b. Switching Time Waveforms

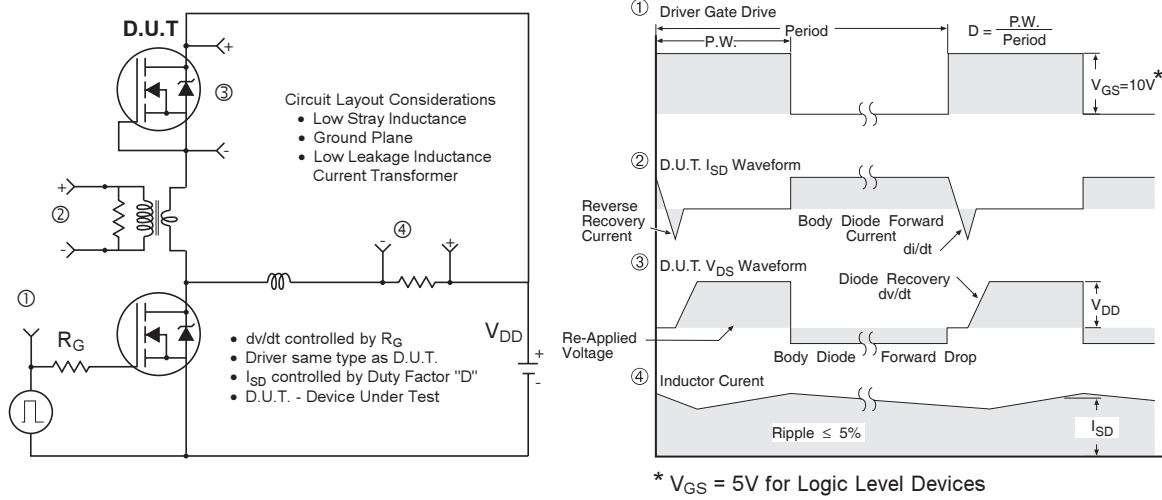


Fig 16. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

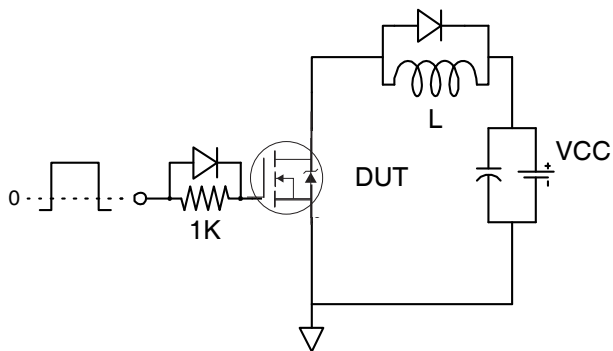


Fig 17. Gate Charge Test Circuit

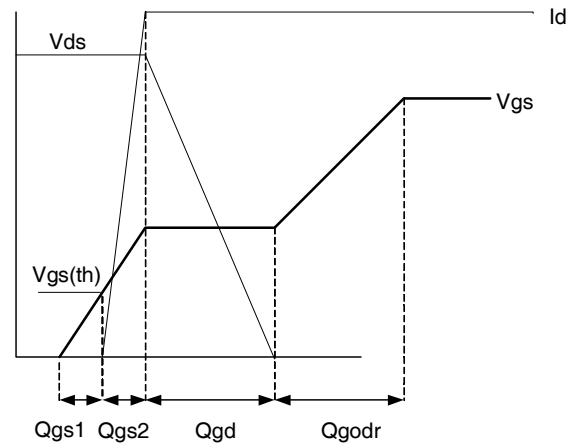
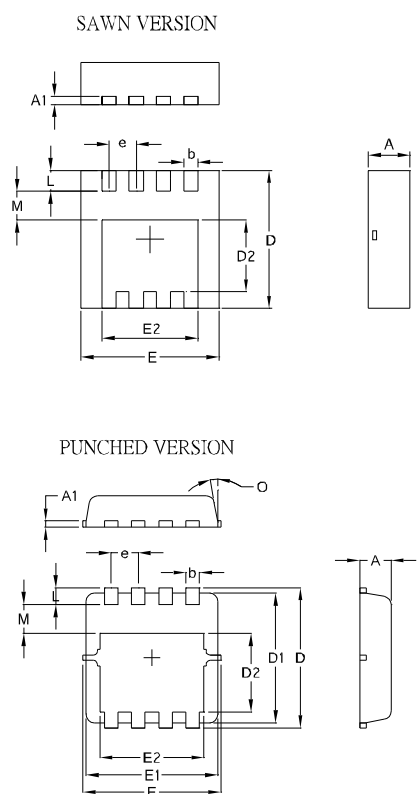


Fig 18. Gate Charge Waveform

PQFN 3.3x3.3 Outline Package Details

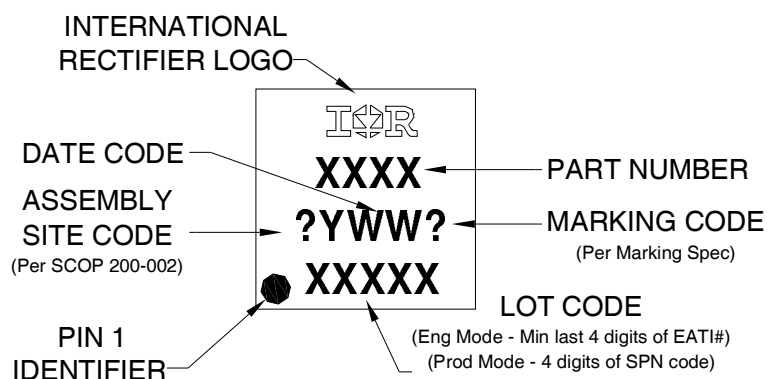


SYMBOL	COMMON			
	MM		INCH	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.05	0.0276	0.0413
A1	0.12	0.39	0.0047	0.0154
b	0.25	0.39	0.0098	0.0154
D	3.20	3.45	0.1260	0.1358
D1	3.00	3.20	0.1181	0.1417
D2	1.69	2.20	0.0665	0.0866
E	3.20	3.40	0.1260	0.1339
E1	3.00	3.20	0.1181	0.1417
E2	2.15	2.59	0.0846	0.1020
e	0.65 BSC		0.0256 BSC	
L	0.15	0.55	0.0059	0.0217
M	0.59	—	0.0232	—
O	9Deg	12Deg	9Deg	12Deg

For footprint and stencil design recommendations, please refer to application note AN-1154 at <http://www.irf.com/technical-info/appnotes/an-1154.pdf>

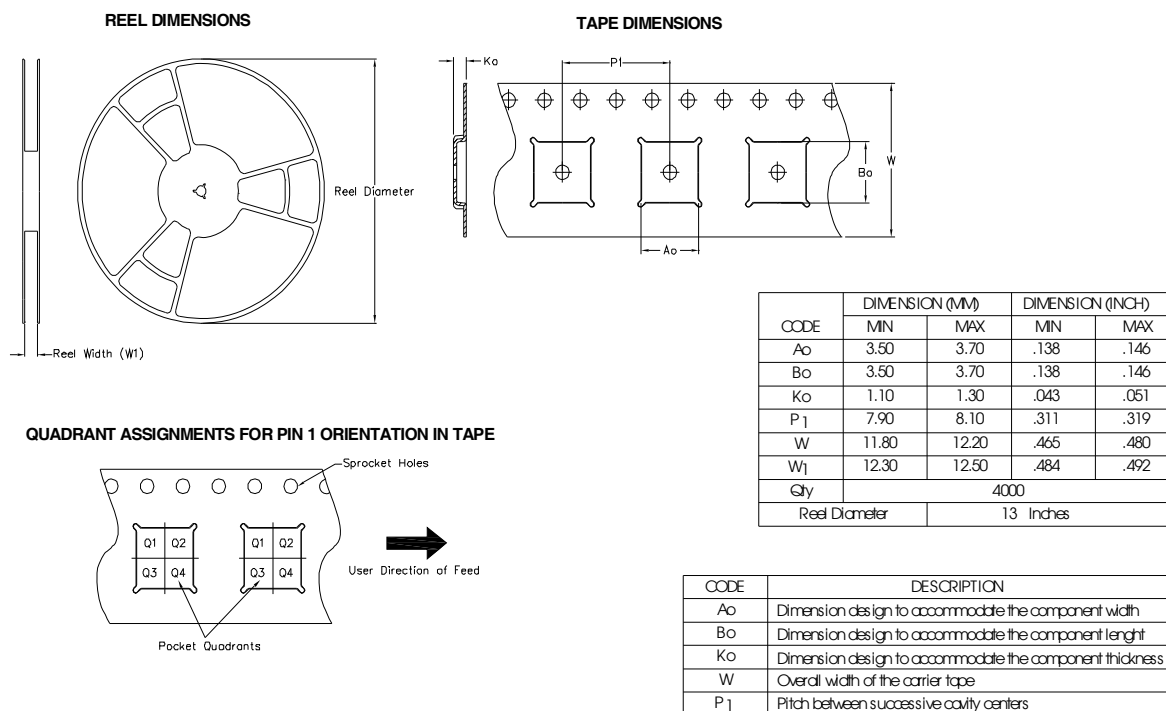
PQFN 3.3x3.3 Part Marking

3.3x3.3 PQFN PART MARKING DETAIL



Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

PQFN 3.3x3.3 Tape and Reel



Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

Qualification Information[†]

Qualification level	Industrial ^{††} (per JEDEC JESD47F ^{†††} guidelines)	
Moisture Sensitivity Level	PQFN 3.3mm x 3.3mm	MSL 1 (per JEDEC J-STD-020D ^{†††})
RoHS Compliant	Yes	

[†] Qualification standards can be found at International Rectifier's web site

<http://www.irf.com/product-info/reliability>

^{††} Higher qualification ratings may be available should the user have such requirements.

Please contact your International Rectifier sales representative for further information:

<http://www.irf.com/whoto-call/salesrep/>

^{†††} Applicable version of JEDEC standard at the time of product release.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^{\circ}\text{C}$, $L = 0.69\text{mH}$, $R_G = 50\Omega$, $I_{AS} = 12\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ R_{θ} is measured at T_J of approximately 90°C .
- ⑤ When mounted on 1 inch square 2 oz copper pad on 1.5x1.5 in. board of FR-4 material.
- ⑥ Calculated continuous current based on maximum allowable junction temperature. Package is limited to 40A by production test capability.

Revision History

Date	Comment
5/14/2014	- Updated ordering information to reflect the End-Of-life (EOL) of the mini-reel option (EOL notice #259) - Updated Package outline on page 7. - Updated Tape and Reel on page 8. - Updated data sheet based on corporate template.
6/5/2014	Updated schematic on page1

International
 Rectifier

IR WORLD HEADQUARTERS: 101 N. Sepulveda Blvd., El Segundo, California 90245, USA

To contact International Rectifier, please visit <http://www.irf.com/whoto-call/>